TECHNICAL DATA DATA SHEET 4780, REV. B

SILICON SCHOTTKY RECTIFIER Ultra Low Reverse Leakage 150°C Operating Temperature

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

Maximum Ratings:

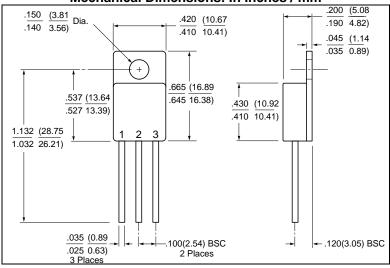
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	60	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form (Single/Doubler)	16	A
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave	280	A
Max. Junction Temperature	TJ	-	-65 to +150	°C
Max. Storage Temperature	T _{stg}	-	-65 to +150	°C
Thermal Resistance	$R_{ ext{ heta}JC}$	-	1.45	°C/W

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V _{F1}	@ 16A, Pulse, T _J = 25 °C	0.79	V
	V _{F2}	@ 16A, Pulse, T _J = 125 °C	0.74	V
Max. Reverse Current	I _{R1}	$@V_{R} = 60V, Pulse,$	2	mA
		T _J = 25 °C		
	I _{R2}	$@V_{R} = 60V$, Pulse,	140	mA
		T _J = 125 °C		
Max. Junction Capacitance	CT	@V _R = 5V, T _C = 25 °C	800	pF
		f _{SIG} = 1MHz,		
		$V_{SIG} = 50 \text{mV} (\text{p-p})$		

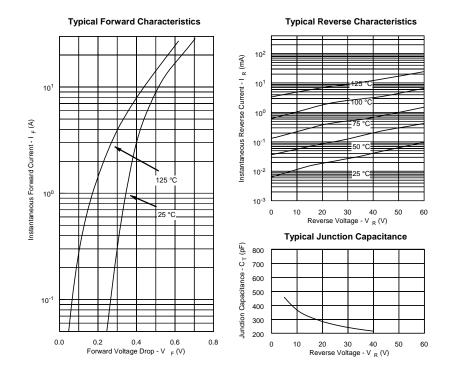
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TO-257

DEVICE TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE
COMMON CATHODE (P)	ANODE 1	COMMON CATHODE	ANODE 2
COMMON ANODE (N)	CATHODE 1	COMMON ANODE	CATHODE 2
DOUBLER (D)	ANODE	CATHODE / ANODE	CATHODE



SHD126213 SHD126213D SHD126213N SHD126213P

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